



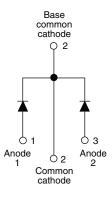
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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 16 A



TO-247AC



PRODUCT SUMMARY					
Package	TO-247AC				
I _{F(AV)}	2 x 16 A				
V_{R}	1200 V				
V _F at I _F	2.3 V				
t _{rr} typ.	30 ns				
T _J max.	150 °C				
Diode variation	Single die				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA32PA120C... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A per leg continuous current, the VS-HFA32PA120C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA32PA120C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V_{R}		1200	V		
Maximum continuous forward current per leg	- I _F	T _C = 100 °C	16	А		
per device			32			
Single pulse forward current	I _{FSM}		190			
Maximum repetitive forward current	I _{FRM}		64			
Maximum navvar dissination	-	T _C = 25 °C	151	°C		
Maximum power dissipation	P_{D}	T _C = 100 °C	60]		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	W		



VS-HFA32PA120CPbF, VS-HFA32PA120C-N3

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		1200	-	-	
Maximum forward voltage	V _{FM}	I _F = 16 A	See fig. 1	=	2.5	3.0	V
		I _F = 32 A		=	3.2	3.93	
		I _F = 16 A, T _J = 125 °C		=	2.3	2.7	
Maximum reverse	,	V _R = V _R rated	Soo fig. 0	-	0.75	20	
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	375	2000	μΑ
Junction capacitance	C _T	V _R = 200 V	See fig. 3	=	27	40	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	A/μs, V _R = 30 V	-	30	-		
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	90	135	ns	
occ lig. 5, 10	t _{rr2}	T _J = 125 °C	I _F = 16 A	-	164	245		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	5.8	10	- A	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 200 \text{ V}$	-	260	675		
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	680	1838	nC	
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	120	-	- A/µs	
	dI _{(rec)M} /dt2	T _J = 125 °C		-	76	-	μs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	0.83		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-		
Woight			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC (JEDEC)	HFA32PA120C			•	

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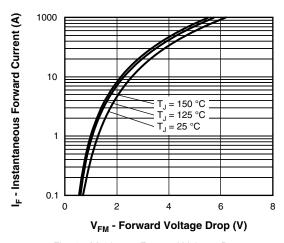


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

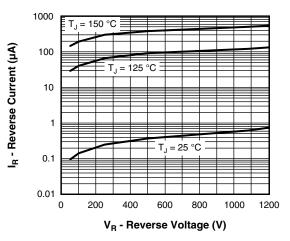


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

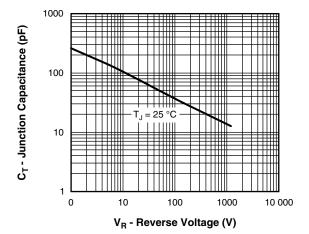


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

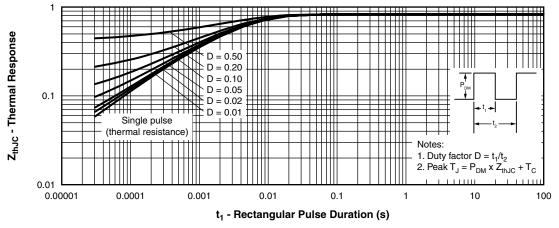


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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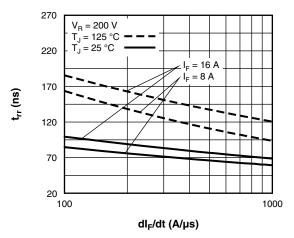


Fig. 5 - Typical Reverse Recovery Time vs. dl_E/dt (Per Leg)

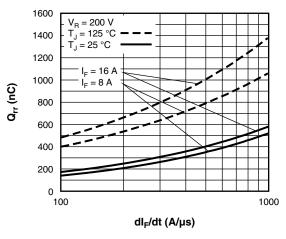


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

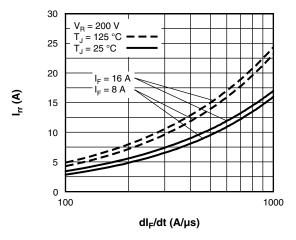


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

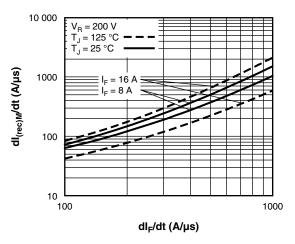


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

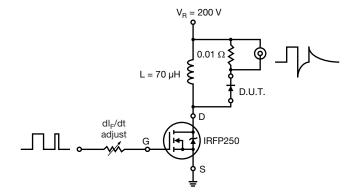
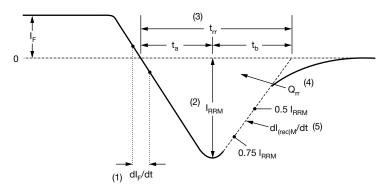


Fig. 9 - Reverse Recovery Parameter Test Circuit

VS-HFA32PA120CPbF, VS-HFA32PA120C-N3

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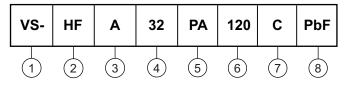


- (1) dl_F/dt rate of change of current through zero crossing
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- HEXFRED® family
- Electron irradiated
- Current rating (32 = 32 A)
- **5** PA = TO-247AC
- 6 Voltage rating: (120 = 1200 V)
- Circuit configuration
 C = common cathode
- 8 Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

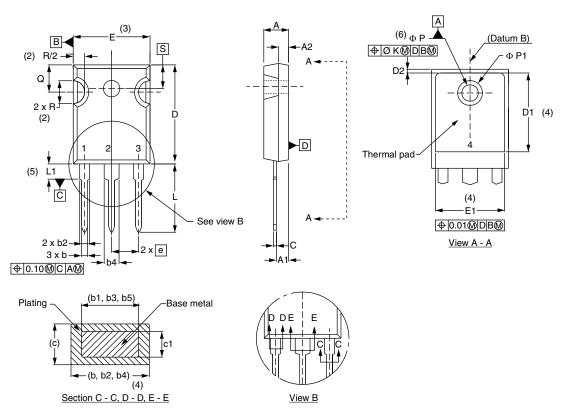
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA32PA120CPbF	25	500	Antistatic plastic tube				
VS-HFA32PA120C-N3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95542			
Part marking information	TO-247ACPbF	www.vishay.com/doc?95226			
Part marking information	TO-247AC-N3	www.vishay.com/doc?95007			

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TO-247AC - 50 mils L/F

DIMENSIONS in millimeters and inches



MILLIM	IETERS	INC	HES	NOTES
MIN.	MAX.	MIN.	MAX.	NOTES
4.65	5.31	0.183	0.209	
2.21	2.59	0.087	0.102	
1.17	1.37	0.046	0.054	
0.99	1.40	0.039	0.055	
0.99	1.35	0.039	0.053	
1.65	2.39	0.065	0.094	
1.65	2.34	0.065	0.092	
2.59	3.43	0.102	0.135	
2.59	3.38	0.102	0.133	
0.38	0.89	0.015	0.035	
0.38	0.84	0.015	0.033	
19.71	20.70	0.776	0.815	3
13.08	-	0.515	-	4
	MIN. 4.65 2.21 1.17 0.99 0.99 1.65 1.65 2.59 2.59 0.38 0.38 19.71	4.65 5.31 2.21 2.59 1.17 1.37 0.99 1.40 0.99 1.35 1.65 2.39 1.65 2.34 2.59 3.43 2.59 3.38 0.38 0.89 0.38 0.84 19.71 20.70	MIN. MAX. MIN. 4.65 5.31 0.183 2.21 2.59 0.087 1.17 1.37 0.046 0.99 1.40 0.039 0.99 1.35 0.039 1.65 2.39 0.065 1.65 2.34 0.065 2.59 3.43 0.102 2.59 3.38 0.102 0.38 0.89 0.015 0.38 0.84 0.015 19.71 20.70 0.776	MIN. MAX. MIN. MAX. 4.65 5.31 0.183 0.209 2.21 2.59 0.087 0.102 1.17 1.37 0.046 0.054 0.99 1.40 0.039 0.055 0.99 1.35 0.039 0.053 1.65 2.39 0.065 0.094 1.65 2.34 0.065 0.092 2.59 3.43 0.102 0.135 2.59 3.38 0.102 0.133 0.38 0.89 0.015 0.035 0.38 0.84 0.015 0.033 19.71 20.70 0.776 0.815

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
OTIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
Ш	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215	BSC	
ØK	0.2	254	0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q

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